



DMN3042LFDF

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
	28mΩ @ V _{GS} = 10V	7.0A
30V	32mΩ @ V _{GS} = 4.5V	6.5A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

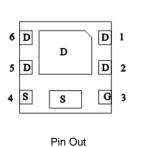
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 Per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.007 grams (Approximate)

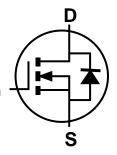
U-DFN2020-6 (Type F)

Top View

Bottom View



Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3042LFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3042LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



S7 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

Date	Code	Key

Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D		Н	I	J	K	L	М	Ν	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



S7 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Da	Dale Code Key												
	Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
	Code	6		0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	Х	Y	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			Vdss	30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	lo	7.0 5.6	А
Maximum Continuous Body Diode Forward Curre	ent (Note 6)		ls	1.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)		ldм	35	А
Avalanche Current (L = 0.1mH) (Note 7)		las	13	А	
Avalanche Energy (L = 0.1mH) (Note 7)			Eas	9	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.7	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	P	177	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	RθJA	124	C/vv	
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.1	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	61	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R _{θJA}	43	C/W	
Thermal Resistance, Junction to Case	Steady State	R _{θJC}	9.3	°C/W	
Operating and Storage Temperature Range		TJ. TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Symbol	IVIIII	тур	IVIAA	Unit	Test condition
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	$V_{GS} = 0V, I_{D} = 250 \mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.6	—	1.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
		_	17	28		$V_{GS} = 10V, I_{D} = 4.0A$
Static Drain-Source On-Resistance	Deserve	_	20	32	mΩ	V _{GS} = 4.5V, I _D = 4.0A
Static Drain-Source On-Resistance	RDS(ON)	_	24	42	11175	V _{GS} = 3.0V, I _D = 4.0A
		_	28	50		Vgs = 2.5V, ID = 4.0A
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss		570	—		
Output Capacitance	Coss		63	—	pF	Vps = 15V, Vgs = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	—	53	—		
Gate Resistance	Rg	_	3.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Qg	—	13.3	—		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	6.1	—	nC	
Gate-Source Charge	Qgs	_	1.0	—	nc	$V_{DS} = 15V, I_D = 6.9A$
Gate-Drain Charge	Q _{gd}	—	1.6	—		
Turn-On Delay Time	t _{D(ON)}	_	1.5	—		
Turn-On Rise Time	tR	_	3.3	—		$V_{GS} = 10V, V_{DD} = 15V, R_{g} = 3\Omega,$
Turn-Off Delay Time	t _{D(OFF)}		13.9	—	ns	I _D = 6.9A
Turn-Off Fall Time	tF		4.9	—	1	
Body Diode Reverse Recovery Time	trr		7.8	—	ns	Is = 5A, dl/dt = 100A/µs
Body Diode Reverse Recovery Charge	Qrr		1.9	—	nC	Is = 5A, dl/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

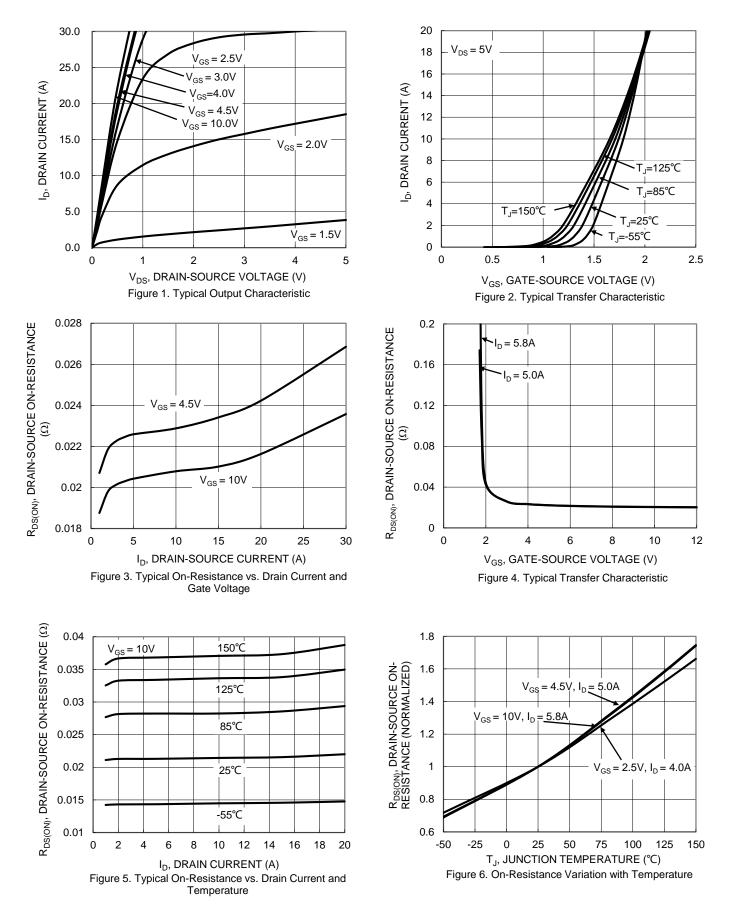
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



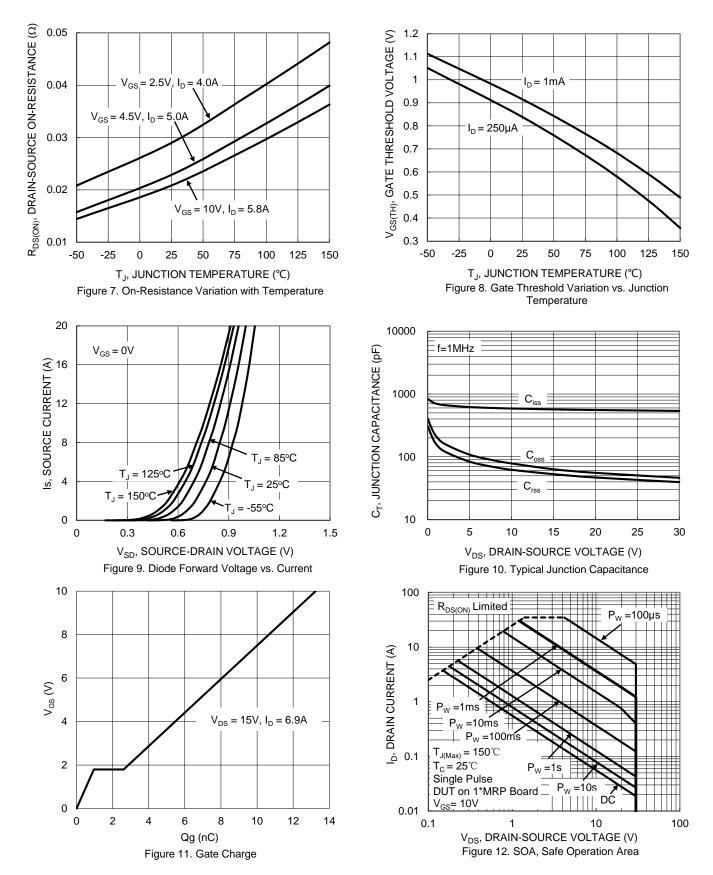
DMN3042LFDF



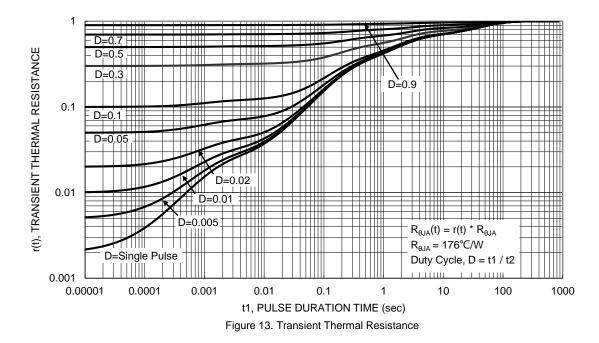
DMN3042LFDF Datasheet number: DS38985 Rev. 2 - 2



DMN3042LFDF



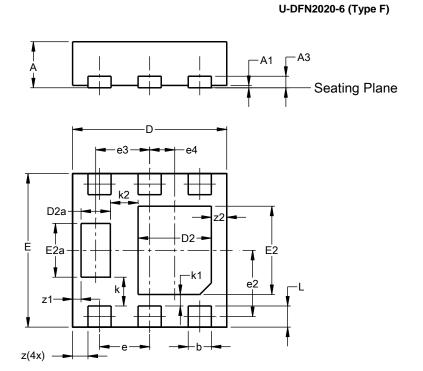






Package Outline Dimensions

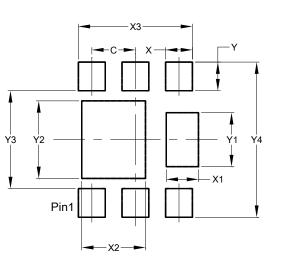
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN2020-6 (Type F)								
Dim	Min Max Typ								
Α	0.57	0.63	0.60						
A1	0.00	0.05	0.03						
A3	-	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
E	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
е	Ť	0.65 BS	С						
e2	C).863 BS	SC						
e3	ł	0.70 BS	С						
e4	C).325 BS	SC						
k	ł	0.37 BS	С						
k1		0.15 BS	С						
k2	Ť	0.36 BS	С						
L	0.225	0.325	0.275						
z		0.20 BS	С						
z1	C).110 BS	SC						
z2		0.20 BS	С						
All D	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Value (in mm)
0.650
0.400
0.480
0.950
1.700
0.425
0.800
1.150

Y3

Y4

1.450

2.300

U-DFN2020-6 (Type F)



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C IPP110N20N3GXK BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2941 NTE2945 NTE2946 NTE2960 NTE2969 NTE2976 NTE6400A NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S STF35N65DM2 STW70N60DM6-4 SSM6P54TU,LF SSM6P69NU,LF DMP22D4UF0-7B DMN1006UCA6-7 DMN16M9UCA6-7